ON Semiconductor®

FDS9958-F085

Dual P-Channel PowerTrench® MOSFET
-60V, -2.9A, 105mΩ

Features

- Max $r_{DS(on)}$ =105mΩ at V_{GS} = -10V, I_D = -2.9A
- Max $r_{DS(on)}$ =135mΩ at V_{GS} = -4.5V, I_D = -2.5A
- Qualified to AEC Q101
- RoHS Compliant

100% RoHS COMPLIANT

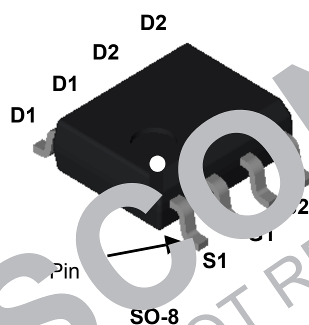
General Description

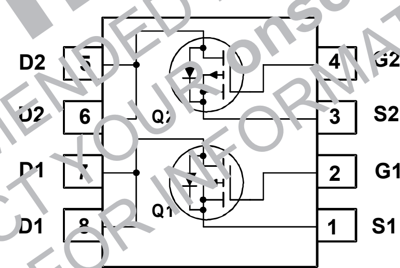
These P-channel logic level specified MOSFETs are produced using ON Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for portable electronics applications: load switching and power management, battery charging and protection circuits.

Applications

- Load Switch
- Power Management





MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		-60	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	Drain Current -Continuous	(Note 1a)	-2.9	A
	-Pulsed		-12	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	54	mJ
P_D	Power Dissipation for Dual Operation		2	W
	Power Dissipation	(Note 1a)	1.6	
	Power Dissipation	(Note 1b)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		40	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	

Package Marking and Ordering Information

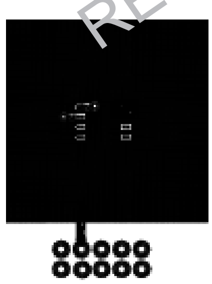
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS9958	FDS9958-F085	SO-8	330mm	12mm	2500units

Electrical Characteristics T_J = 25°C unless otherwise noted

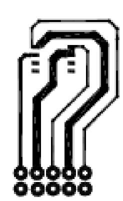
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = -250μA, V_{GS} = 0V	-60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = -250μA, referenced to 25°C		-52		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -48V, V_{GS} = 0V			-1	μA
		V_{DS} = -48V, V_{GS} = 0V, T_J = 125°C			-100	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, I_D = -250μA	-1.0	-1[illegible]	-3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250μA, referenced to 25°C		4		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = -10V, I_D = -2.9A		8[illegible]	105	mΩ
		V_{GS} = -4.5V, I_D = -2.5A		103	135	mΩ
		V_{GS} = -10V, I_D = -2.9A, T_J = 125		131	190	mΩ
g_{FS}	Forward Transconductance	V_{DD} = -5V, I_D = -2.9A		7.7		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -30V, V_{GS} = 0V, f = 1MHz		765	1020	pF
C_{oss}	Output Capacitance			90	120	pF
C_{rss}	Reverse Transfer Capacitance			40	65	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -30V, I_D = -2.9A, V_{GS} = -10V, R_{GEN} = 6Ω		6	12	ns
t_r	Rise Time			3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			27	43	ns
t_f	Fall Time			6	12	ns
Q_g	Total Gate Charge	V_{GS} = 0V to -10V, V_{DD} = -30V, I_D = -2.9A		16	23	nC
Q_g	Total Gate Charge	V_{GS} = 0V to -4.5V, V_{DD} = -30V, I_D = -2.9A		8	12	nC
Q_{gs}	Gate to Source Charge	V_{DD} = -30V, I_D = -2.9A		2		nC
Q_{gd}	Gate to Drain "Miller" Charge			3		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = -1.3A (Note 2)		-0.8	-1.2	V
t_{rr}	Reverse Recovery Time	I_F = -2.9A, di/dt = 100A/μs		26	42	ns
Q_{rr}	Reverse Recovery Charge			21	35	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 1 in² pad of 2 oz copper



b) 135°C/W when mounted on a minimun pad

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

3. UIL condition: Starting T_J = 25°C, L = 3mH, I_{AS} = 6A, V_{DD} = 60V, V_{GS} = 10V.

Typical Characteristics T_J = 25°C unless otherwise noted

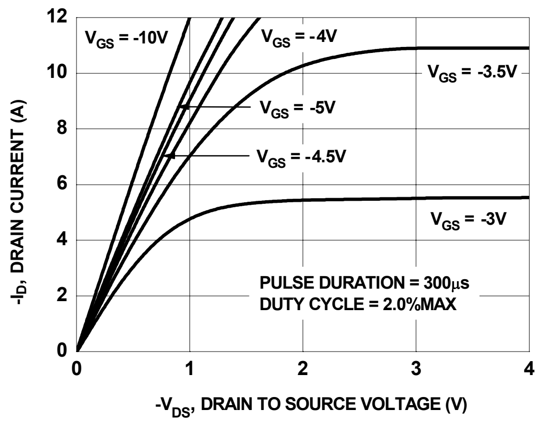


Figure 1. On-Region Characteristics

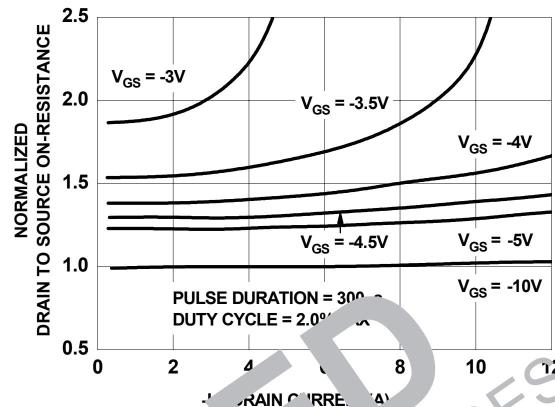


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

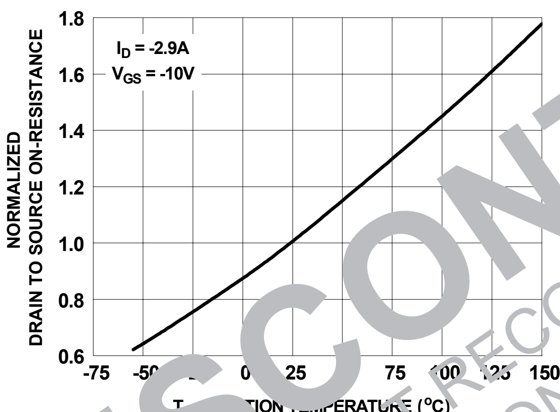


Figure 3. Normalized On-Resistance vs Junction Temperature

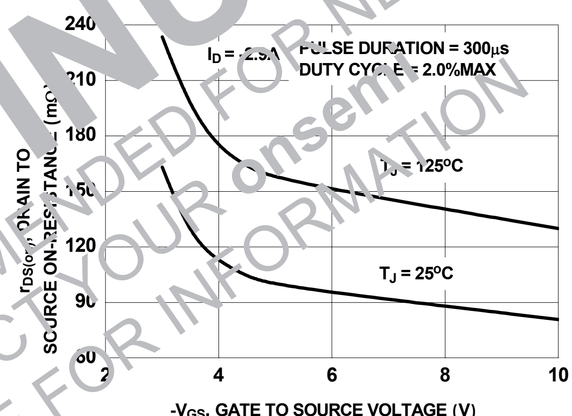


Figure 4. On-Resistance vs Gate to Source Voltage

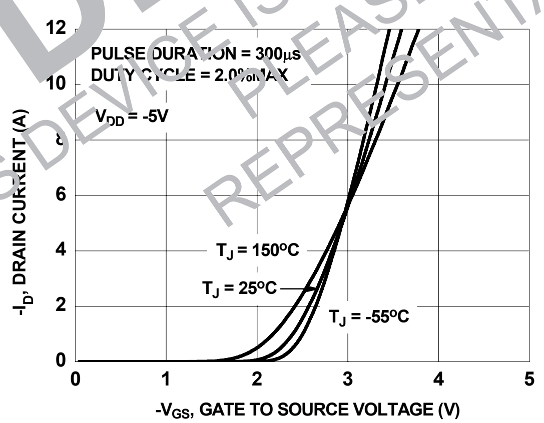


Figure 5. Transfer Characteristics

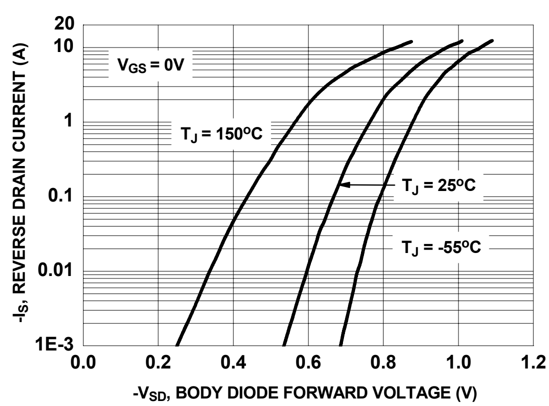


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

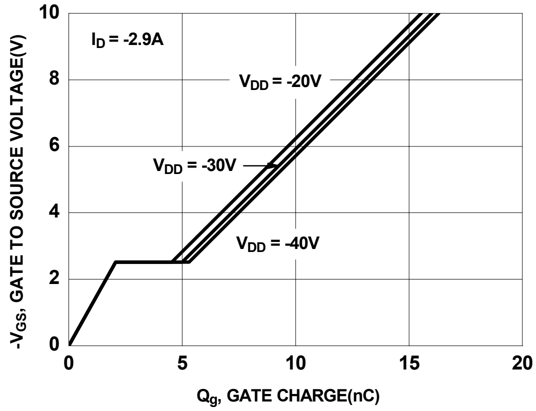


Figure 7. Gate Charge Characteristics

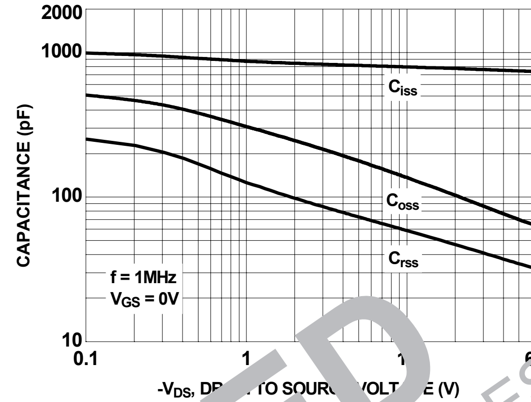


Figure 8. Capacitance vs Drain to Source Voltage

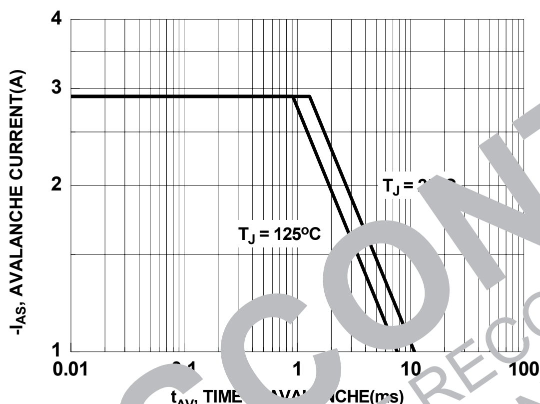


Figure 9. Unclamped Inductive Switching Capability

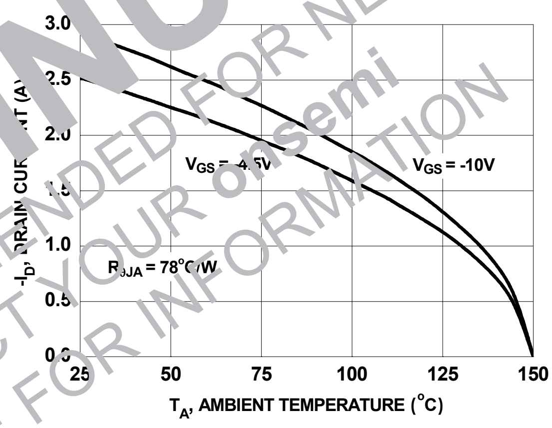


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

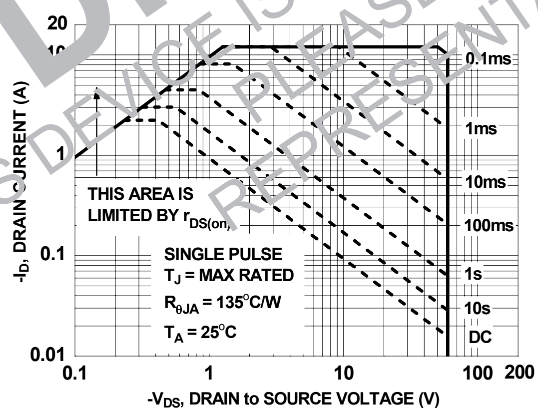


Figure 11. Forward Bias Safe Operating Area

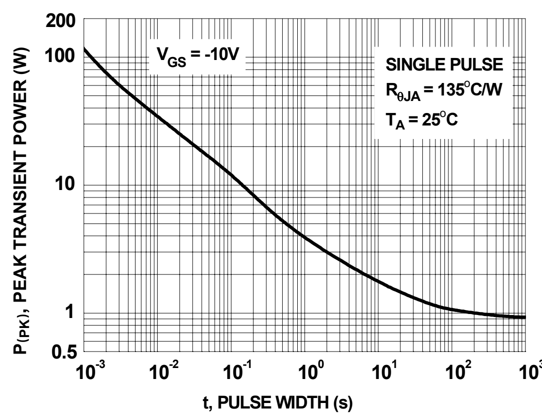


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

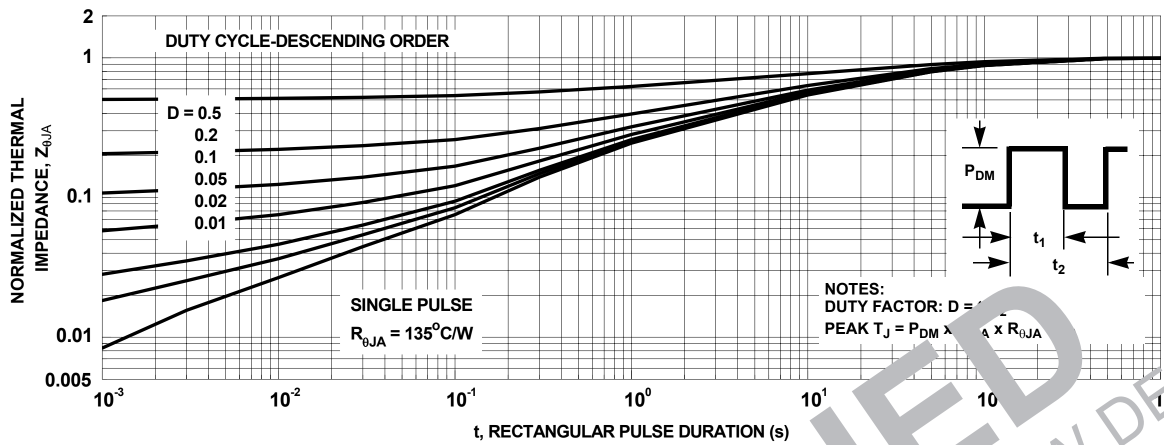


Figure 13. Transient Thermal Response Curve

PUBLICATION ORDERING INFORMATION

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